Bo Song

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

29	1,349	15	34
papers	citations	h-index	g-index
34	1,555	3.7	3.75
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
29	Distributed polarization-doped GaN p□ diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. *Applied Physics Letters*, **2022**, 120, 122111	3.4	0
28	Steep Sub-Boltzmann Switching in AlGaN/GaN Phase-FETs With ALD VO2. *IEEE Transactions on Electron Devices*, **2018**, 65, 945-949	2.9	11
27	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. *Applied Physics Letters*, **2017**, 110, 063501	3.4	34
26	Electron mobility in polarization-doped Al0-0.2GaN with a low concentration near 1017 cm□. *Applied Physics Letters*, **2017**, 110, 182102	3.4	8
25	Ultralow-Leakage AlGaN/GaN High Electron Mobility Transistors on Si With Non-Alloyed Regrown Ohmic Contacts. *IEEE Electron Device Letters*, **2016**, 37, 16-19	4.4	26
24	1.7-kV and 0.55- $text{m}Omega cdot text {cm}^{2}$ GaN p-n Diodes on Bulk GaN Substrates With Avalanche Capability. *IEEE Electron Device Letters*, **2016**, 37, 161-164	4.4	125
23	Comparing buffer leakage in PolarMOSH on SiC and free-standing GaN substrates **2016**,		1
22	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates **2015**,		3
21	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and 15N isotopes. *Applied Physics Letters*, **2015**, 106, 041906	3.4	10
20	Unique opportunity to harness polarization in GaN to override the conventional power electronics figure-of-merits **2015**,		5
19	Esaki Diodes in van der Waals Heterojunctions with Broken-Gap Energy Band Alignment. *Nano Letters*, **2015**, 15, 5791-8	11.5	237
18	Near unity ideality factor and Shockley-Read-Hall lifetime in GaN-on-GaN p-n diodes with avalanche breakdown. *Applied Physics Letters*, **2015**, 107, 243501	3.4	117
17	High breakdown single-crystal GaN p-n diodes by molecular beam epitaxy. *Applied Physics Letters*, **2015**, 107, 232101	3.4	44
16	. *IEEE Electron Device Letters*, **2015**, 36, 375-377	4.4	126
15	AlGaN/GaN HEMTs on Si by MBE with regrown contacts and fT = 153 GHz. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 887-889		8
14	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. *Applied Physics Letters*, **2014**, 104, 193506	3.4	35
13	. *IEEE Transactions on Electron Devices*, **2014**, 61, 747-754	2.9	23

12	GaN lateral PolarSJs: Polarization-doped super junctions **2014**,		2
11	Impact of CF4plasma treatment on threshold voltage and mobility in Al2O3/InAlN/GaN MOSHEMTs. *Applied Physics Express*, **2014**, 7, 031002	2.4	15
10	Gate-recessed integrated E/D GaN HEMT technology with fT/fmax >300 GHz. *IEEE Electron Device Letters*, **2013**, 34, 741-743	4.4	70
9	Polarization-Induced GaN-on-Insulator E/D Mode p-Channel Heterostructure FETs. *IEEE Electron Device Letters*, **2013**, 34, 852-854	4.4	49
8	Ultrascaled InAlN/GaN High Electron Mobility Transistors with Cutoff Frequency of 400 GHz. *Japanese Journal of Applied Physics*, **2013**, 52, 08JN14	1.4	55
7	High Holding Voltage SCR-LDMOS Stacking Structure With Ring-Resistance-Triggered Technique. *IEEE Electron Device Letters*, **2013**, 34, 1178-1180	4.4	35
6	Quaternary Barrier InAlGaN HEMTs With f_{T}/f_{max} of 230/300 GHz. *IEEE Electron Device Letters*, **2013**, 34, 378-380	4.4	42
5	InAlN/AlN/GaN HEMTs With Regrown Ohmic Contacts and f_{T} of 370 GHz. *IEEE Electron Device Letters*, **2012**, 33, 988-990	4.4	252
4	Monolithically integrated E/D-mode InAlN HEMTs with [illegible]/[illegible]max > 200/220 GHz **2012**,		5
3	Trigger voltage walk-in effect of ESD protection device in HVCMOS **2010**,		2
2	A Novel Capacitance-Coupling-Triggered SCR for Low-Voltage ESD Protection Applications. *IEEE Electron Device Letters*, **2010**, 31, 1089-1091	4.4	4
1	Compact MOS-triggered SCR with faster turn-on speed for ESD protection. *Microelectronics Reliability*, **2010**, 50, 1393-1397	1.2	5